

SANYO	No.3465	2SK1462
		N-Channel MOS Silicon FET

Very High-Speed Switching Applications

Features

- Low ON-state resistance.
- Very high-speed switching.
- Converters.

Absolute Maximum Ratings at Ta=25°C

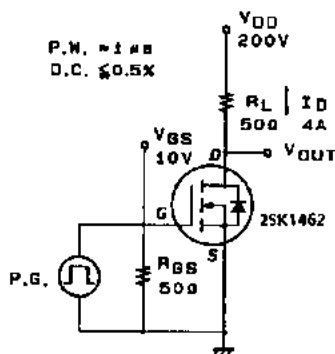
			unit
Drain to Source Voltage	V _{DSS}	900	V
Gate to Source Voltage	V _{GSS}	±30	V
Drain Current(DC)	I _D	8	A
Drain Current(Pulse)	I _{DP}	PW ≤ 10μs, duty cycle ≤ 1%	16 A
Allowable Power Dissipation	P _D	Tc=25°C	150 W
			2.5 W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Electrical Characteristics at Ta=25°C

			min	typ	max	unit
D-S Breakdown Voltage	V _{(BR)DSS}	I _D =1mA, V _{GS} =0	900			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =900V, V _{GS} =0			1.0	mA
Gate to Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0			±100	nA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	2.0		3.0	V
Forward Transfer Admittance	Y _{fs}	V _{DS} =20V, I _D =4A	2.5	5.0		S
Static Drain to Source on State Resistance	R _{DS(on)}	I _D =4A, V _{GS} =10V		1.2	1.6	Ω
Input Capacitance	C _{iss}	V _{DS} =20V, f=1MHz		1600		pF
Output Capacitance	C _{oss}	V _{DS} =20V, f=1MHz		500		pF
Reverse Transfer Capacitance	C _{rss}	V _{DS} =20V, f=1MHz		350		pF
Turn-ON Delay Time	t _{d(on)}	I _D =4A, V _{GS} =10V V _{DD} =200V, R _{GS} =50Ω		20		ns
Rise Time	t _r		80		ns	
Turn-OFF Delay Time	t _{d(off)}		350		ns	
Fall Time	t _f		150		ns	
Diode Forward Voltage	V _{SD}		I _S =8A, V _{GS} =0			1.8

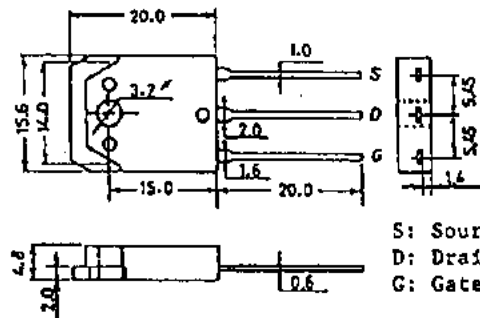
(Note) Be careful in handling the 2SK1462 because it has no protection diode between gate and source.

Switching Time Test Circuit



Package Dimensions 2056

(unit: mm)



SANYO: TO3PB